

## TRANSISTOR (PNP)

### FEATURES

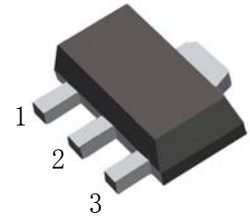
- High voltage:  $V_{CE0}=-60V$
- High transistors frequency

### MAXIMUM RATINGS ( $T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-80	V
$V_{CEO}$	Collector-Emitter Voltage	-60	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-1	A
$P_C$	Collector power dissipation	500	mW
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature	-55-150	$^{\circ}C$

### SOT-89

1. BASE
2. COLLECTOR
3. EMITTER



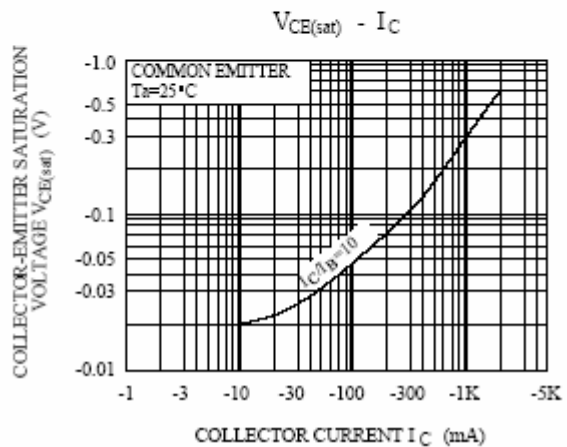
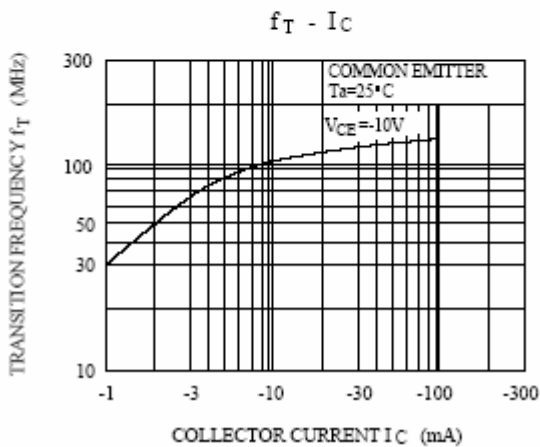
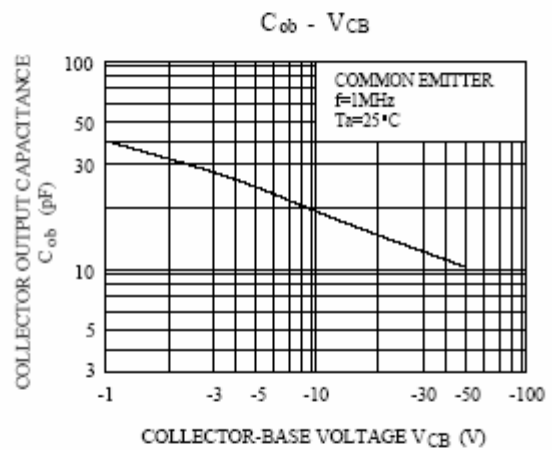
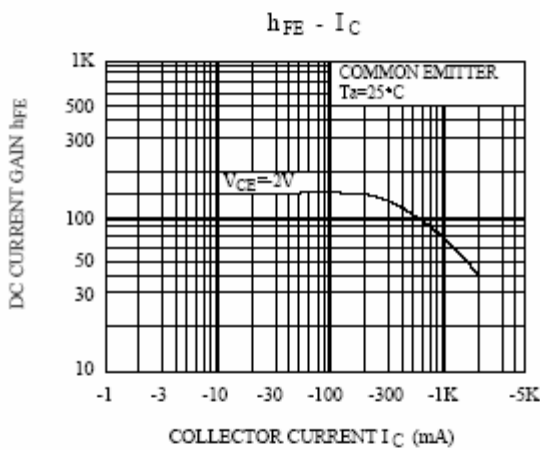
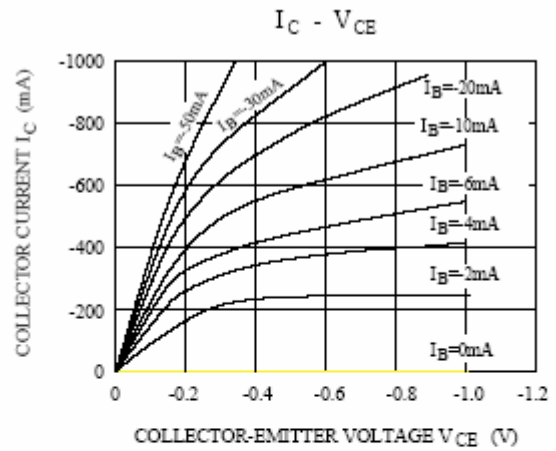
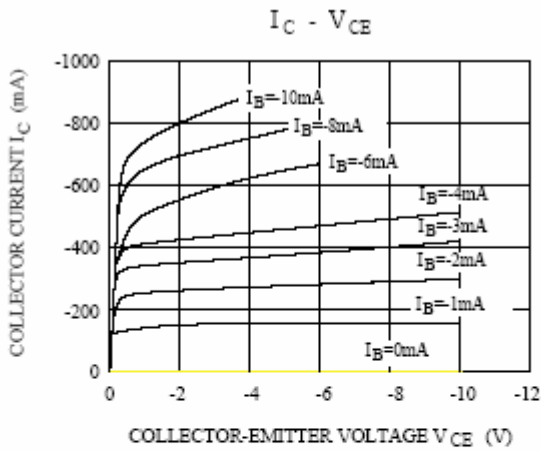
### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.1mA, I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.1mA, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-50V, I_E=0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-4V, I_C=0$			-0.1	$\mu A$
DC current gain	$h_{FE1}$	$V_{CE}=-2V, I_C=-50mA$	60		200	
	$h_{FE2}$	$V_{CE}=-2V, I_C=-1A$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$			-0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-500mA, I_B=-50mA$			-1.2	V
Transition frequency	$f_T$	$V_{CE}=-10V, I_C=-50mA, f=100MHz$		150		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-10V, I_E=0, f=1MHz$		12		pF

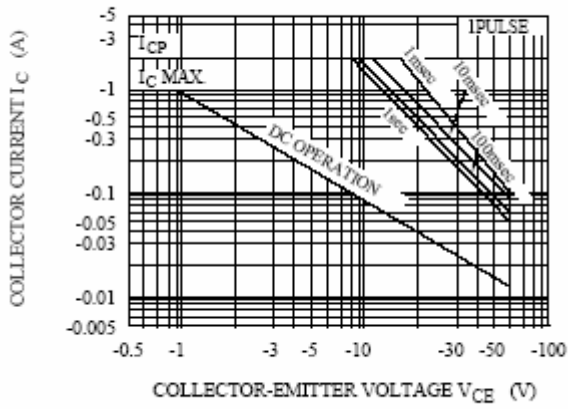
### CLASSIFICATION OF $h_{FE}$

Rank	O	Y
Range	60-120	100-200
Marking	JO	JY

## Typical Characteristics



SAFE OPERATING AREA



$P_C - T_a$

